

ABSTRACT

[0042] A cleaning apparatus of a high-density plasma chemical vapor deposition chamber, and a cleaning method thereof, uniformly and sufficiently supplies a cleaning gas into a chamber to uniformly clean the chamber. The cleaning apparatus includes a chamber, an upper electrode provided in an upper portion of the chamber and applied with radio frequency energy, a lower electrode provided below the upper electrode and applied with radio frequency energy, a chuck provided below the upper electrode and formed thereon with the lower electrode to fix a wafer thereon, and three or more cleaning gas nozzles provided at regular intervals on the sidewall of the chamber around the chuck.